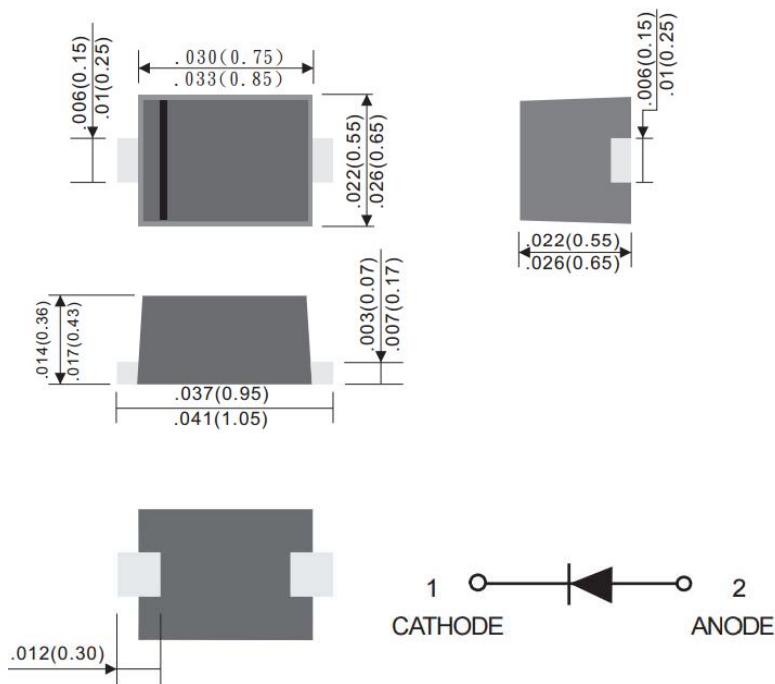




Switching Diodes

Applications

- High speed switching

Features

- Extremely small surface mounting type.
- High Speed.
- High reliability.

Construction

- Silicon epitaxial planar
- Pb-Free package is available
- RoHS product for packing code suffix "G"
- Halogen free product for packing code suffix "H"
- Moisture Sensitivity Level 1

MARKING: 3

Maximum Ratings ($T_A=25^{\circ}\text{C}$ unless otherwise specified)			
Parameter	Symbol	Limit	Unit
Peak reverse voltage	V_{RM}	90	V
DC reverse voltage	V_R	80	V
Peak forward current	I_{FM}	225	mA
Mean rectifying current	I_O	100	mA
Surge current (1s)	I_{surge}	500	mA
Junction Temperature	T_J	125	$^{\circ}\text{C}$
Operating/ Storage Temperature Range	T_{STG}	-55~+150	$^{\circ}\text{C}$

Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise specified)						
Parameter	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	$I_F=100\text{mA}$	—	—	1.2	V
Reverse Current	I_R	$V_R=80\text{V}$	—	—	0.1	μA
Capacitance Between Terminals	C_T	$V_R=0.5\text{V}$, $f=1\text{MHz}$	—	—	3	pF
Reveres Recovery Time	t_{rr}	$V_R=6\text{V}$, $I_F=10\text{mA}$ $R_L=100\Omega$	—	—	4	ns

ELECTRICAL CHARACTERISTIC CURVES

($T_a = 25^\circ\text{C}$)

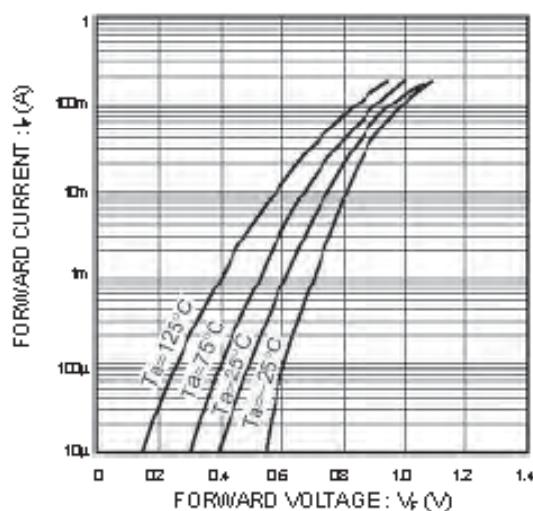


Fig.1 Forward characteristics

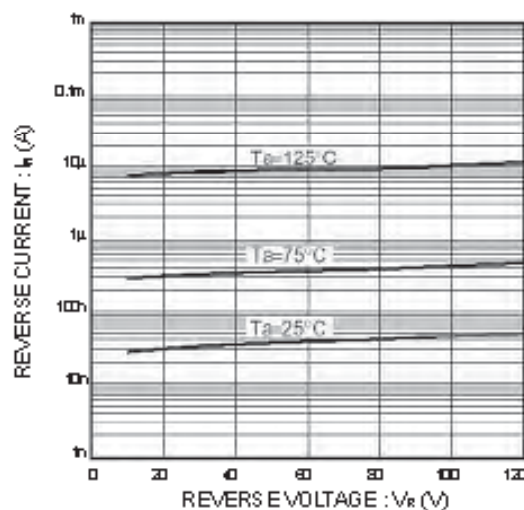


Fig.2 Reverse characteristics

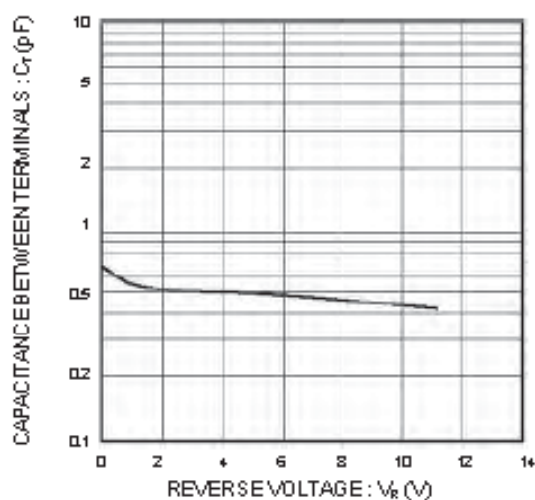


Fig.3 Capacitance between terminals

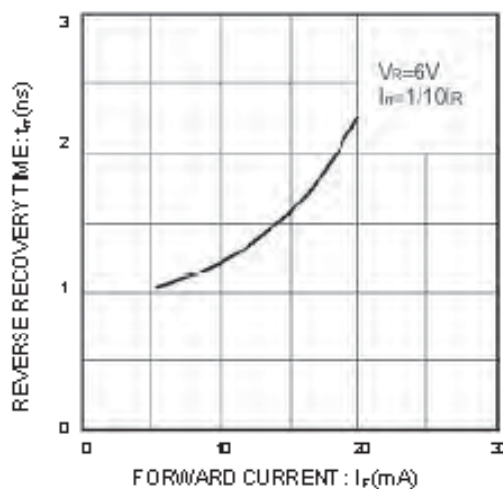


Fig.4 Reverse recovery time characteristics

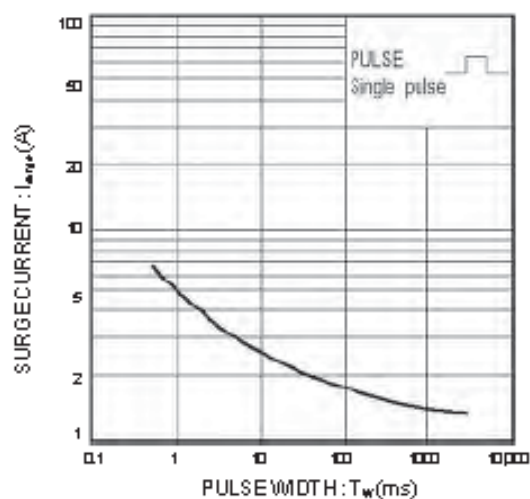


Fig.5 Surge current characteristics

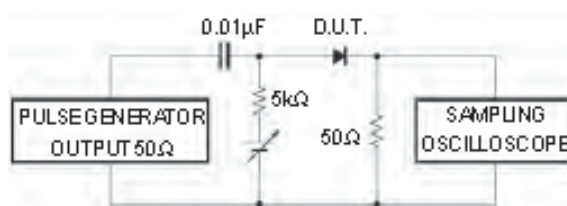


Fig.6 Reverse recovery time (t_r) measurement circuit